



# BUK9K29-100E

## Dual N-channel TrenchMOS logic level FET

28 March 2013

Product data sheet

### 1. General description

Dual logic level N-channel MOSFET in a LFAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)} > 0.5 \text{ V @ } 175 \text{ °C}$

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick reference data

| Symbol                                       | Parameter                        | Conditions  | Min | Typ  | Max | Unit |
|--|----------------------------------|---|-----|------|-----|------|
| $V_{DS}$                                     | drain-source voltage             | $T_j \geq 25 \text{ °C}; T_j \leq 175 \text{ °C}$   | -   | -    | 100 | V    |
| $I_D$  | drain current                    | $V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C}; \text{Fig. 1}$   | -   | -    | 30  | A    |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25 \text{ °C}; \text{Fig. 2}$   | -   | -    | 68  | W    |
| $T_j$  | junction temperature             |   | -55 | -    | 175 | °C   |
| <b>Static characteristics FET1 and FET2</b>  |                                  |   |     |      |     |      |
| $R_{DSon}$                                   | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; \text{Fig. 12}$  | -   | 25.1 | 29  | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |   |     |      |     |      |
| $Q_{G(tot)}$                                 | total gate charge                | $I_D = 10 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{Fig. 14}; \text{Fig. 15}$ | -   | 54   | -   | nC   |
| $Q_{GD}$                                     | gate-drain charge                |   | -   | 10.9 | -   | nC   |

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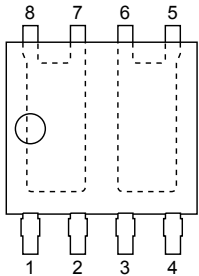
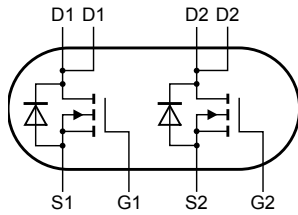
| Symbol                                    | Parameter                                    | Conditions  | Min    | Typ | Max | Unit  |
|---|--|---|--------|-----|-----|-------|
| <b>Avalanche Ruggedness FET1 and FET2</b> |  |   |        |     |     |       |
| $E_{DS(AL)S}$                             | non-repetitive drain-source avalanche energy | $I_D = 30\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $V_{GS} = 5\text{ V}$ ;<br>$T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; Fig. 3 | [1][2] | -   | -   | 83 mJ |

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline   | Graphic symbol   |
|-----|--------|-------------|--|--|
| 1   | S1     | source1     |  <p>LFPAK56D (SOT1205)</p> |  <p>mbk725</p> |
| 2   | G1     | gate1       |  |  |
| 3   | S2     | source2     |  |  |
| 4   | G2     | gate2       |  |  |
| 5   | D2     | drain2      |  |  |
| 6   | D2     | drain2      |  |  |
| 7   | D1     | drain1      |  |  |
| 8   | D1     | drain1      |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package  |  | Version |
|--------------|----------|--|---------|
|              | Name     | Description  |         |
| BUK9K29-100E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK9K29-100E | 9291E        |

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

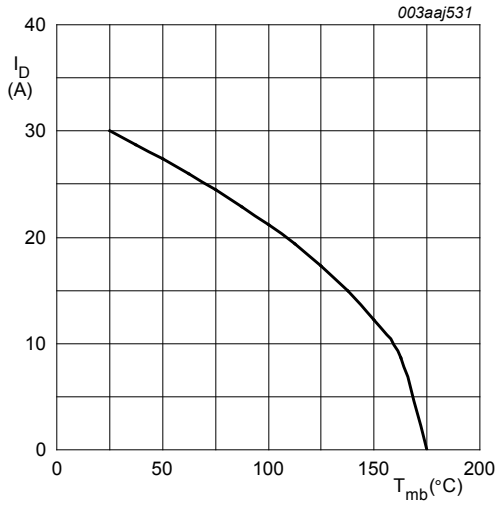
| Symbol                                    | Parameter                                    | Conditions  |        | Min | Max | Unit |
|---|--|---|--------|-----|-----|------|
| $V_{DS}$                                  | drain-source voltage                         | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$  |        | -   | 100 | V    |
| $V_{DGR}$                                 | drain-gate voltage                           | $R_{GS} = 20\text{ k}\Omega$ ; $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                 |        | -   | 100 | V    |
| $V_{GS}$                                  | gate-source voltage                          | $T_j \leq 175\text{ °C}$ ; DC   |        | -10 | 10  | V    |
|   |  | $T_j \leq 175\text{ °C}$ ; Pulsed   | [1][2] | -15 | 15  | V    |
| $I_D$                                     | drain current                                | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 1  |        | -   | 30  | A    |
|   |  | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 1   |        | -   | 21  | A    |
| $I_{DM}$                                  | peak drain current                           | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; Fig. 4                                       |        | -   | 118 | A    |
| $P_{tot}$                                 | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; Fig. 2  |        | -   | 68  | W    |
| $T_{stg}$                                 | storage temperature                          |   |        | -55 | 175 | °C   |
| $T_j$                                     | junction temperature                         |   |        | -55 | 175 | °C   |
| $T_{sld(M)}$                              | peak soldering temperature                   |   |        | -   | 260 | °C   |
| <b>Source-drain diode FET1 and FET2</b>   |  |   |        |     |     |      |
| $I_S$                                     | source current                               | $T_{mb} = 25\text{ °C}$   |        | -   | 30  | A    |
| $I_{SM}$                                  | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$  |        | -   | 118 | A    |
| <b>Avalanche Ruggedness FET1 and FET2</b> |  |   |        |     |     |      |
| $E_{DS(AL)S}$                             | non-repetitive drain-source avalanche energy | $I_D = 30\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; Fig. 3 | [3][4] | -   | 83  | mJ   |

[1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm

[2] Significantly longer life times are achieved by lowering  $T_j$  and or  $V_{GS}$ .

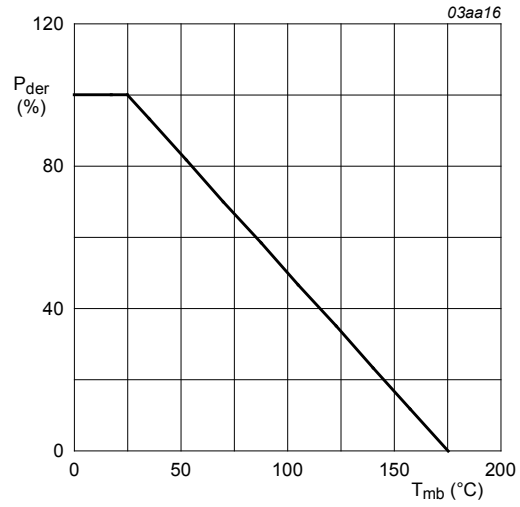
[3] Refer to application note AN10273 for further information

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



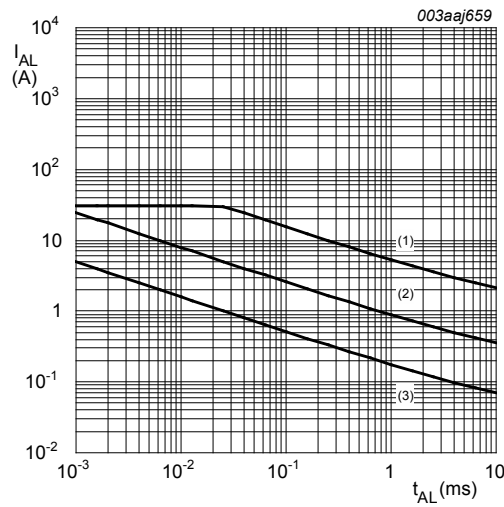
**Fig. 1. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 5V$$



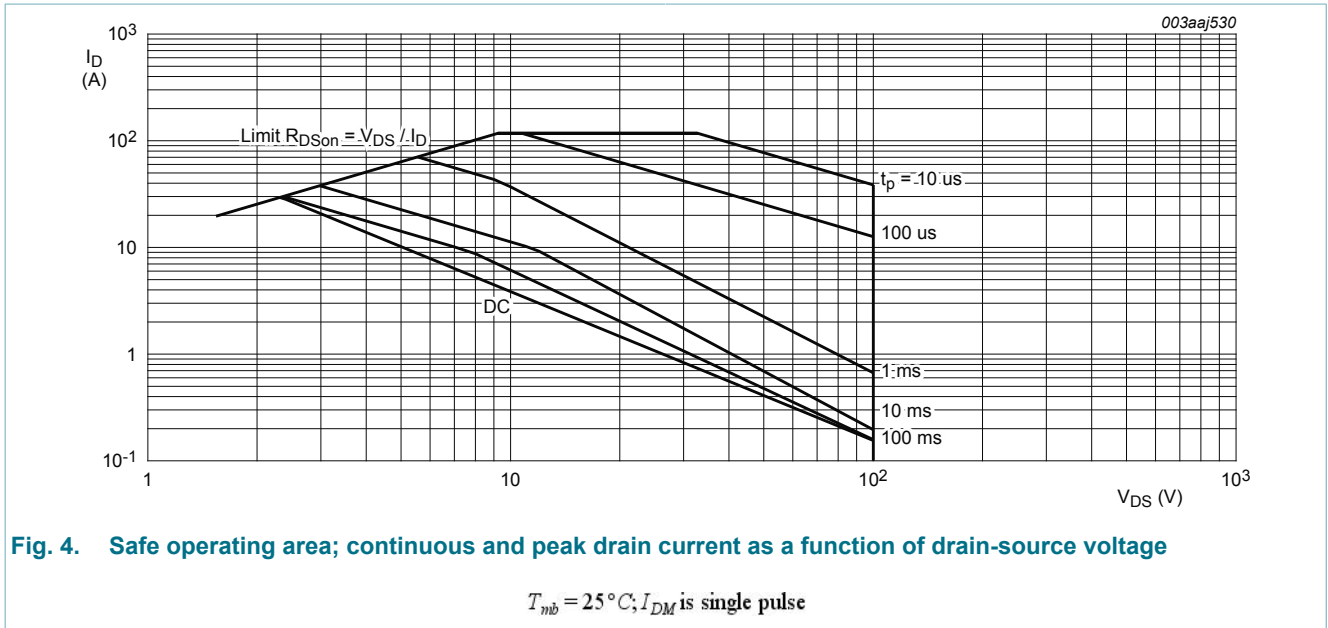
**Fig. 2. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



**Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2**

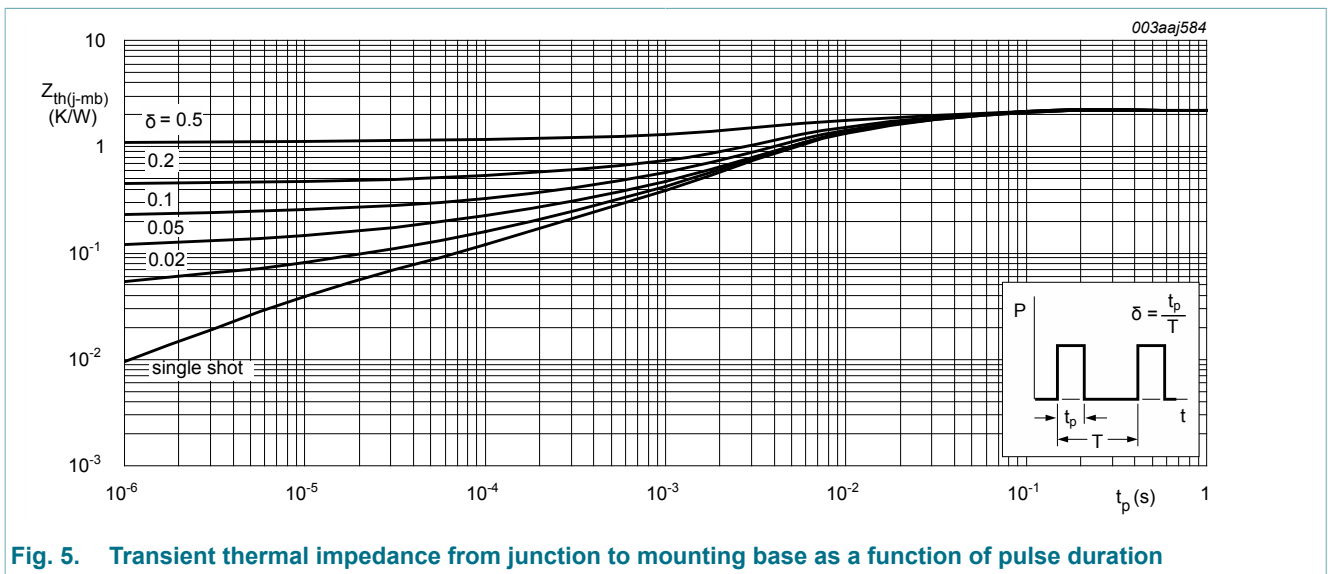
- (1) Single-pulse;  $T_j = 25^{\circ}C$ .
- (2) Single-pulse;  $T_j = 150^{\circ}C$ .
- (3) Repetitive.



## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions  | Min | Typ | Max  | Unit |
|----------------|---|---|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5  | -   | -   | 2.21 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |



## 10. Characteristics

Table 7. Characteristics

| Symbol                                       | Parameter                        | Conditions  | Min | Typ   | Max  | Unit       |
|--|----------------------------------|---|-----|-------|------|------------|
| <b>Static characteristics FET1 and FET2</b>  |                                  |   |     |       |      |            |
| $V_{(BR)DSS}$                                | drain-source breakdown voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$   | 90  | -     | -    | V          |
|  |                                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$  | 100 | -     | -    | V          |
| $V_{GS(th)}$                                 | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>        | 1.4 | 1.7   | 2.1  | V          |
|  |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>       | 0.5 | -     | -    | V          |
|  |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>       | -   | -     | 2.45 | V          |
| $I_{DSS}$                                    | drain leakage current            | $V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$   | -   | 0.02  | 1    | $\mu A$    |
|  |                                  | $V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$  | -   | -     | 500  | $\mu A$    |
| $I_{GSS}$                                    | gate leakage current             | $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$   | -   | 2     | 100  | nA         |
|  |                                  | $V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$  | -   | 2     | 100  | nA         |
| $R_{DS(on)}$                                 | drain-source on-state resistance | $V_{GS} = 5 V; I_D = 5 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 12</a>   | -   | 25.1  | 29   | m $\Omega$ |
|  |                                  | $V_{GS} = 5 V; I_D = 5 A; T_j = 175 \text{ }^\circ C;$<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                   | -   | 68.02 | 80   | m $\Omega$ |
|  |                                  | $V_{GS} = 10 V; I_D = 5 A; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 12</a>  | -   | 22.7  | 27   | m $\Omega$ |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |   |     |       |      |            |
| $Q_{G(tot)}$                                 | total gate charge                | $I_D = 10 A; V_{DS} = 80 V; V_{GS} = 10 V;$<br>$T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a> | -   | 54    | -    | nC         |
| $Q_{GS}$                                     | gate-source charge               | $I_D = 10 A; V_{DS} = 80 V; V_{GS} = 10 V;$<br>$T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 15</a> ; <a href="#">Fig. 14</a> | -   | 5.6   | -    | nC         |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 10 A; V_{DS} = 80 V; V_{GS} = 10 V;$<br>$T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a> | -   | 10.9  | -    | nC         |
| $C_{iss}$                                    | input capacitance                | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 16</a>                     | -   | 2727  | 3637 | pF         |
| $C_{oss}$                                    | output capacitance               |   | -   | 169   | 203  | pF         |
| $C_{rss}$                                    | reverse transfer capacitance     |   | -   | 106   | 145  | pF         |
| $t_{d(on)}$                                  | turn-on delay time               | $V_{DS} = 80 V; R_L = 8 \Omega; V_{GS} = 10 V;$<br>$R_{G(ext)} = 5 \Omega; T_j = 25 \text{ }^\circ C; I_D = 10 A$             | -   | 6.1   | -    | ns         |
| $t_r$  | rise time                        |   | -   | 6.4   | -    | ns         |
| $t_{d(off)}$                                 | turn-off delay time              |   | -   | 67.3  | -    | ns         |
| $t_f$  | fall time                        |   | -   | 35.1  | -    | ns         |
| <b>Source-drain diode FET1 and FET2</b>      |                                  |   |     |       |      |            |
| $V_{SD}$                                     | source-drain voltage             | $I_S = 15 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 17</a>  | -   | 0.78  | 1.2  | V          |

| Symbol   | Parameter             | Conditions   | Min | Typ  | Max | Unit |
|----------|-----------------------|--|-----|------|-----|------|
| $t_{rr}$ | reverse recovery time | $I_S = 10 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; | -   | 32.7 | -   | ns   |
| $Q_r$    | recovered charge      | $V_{DS} = 50 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | -   | 50.1 | -   | nC   |

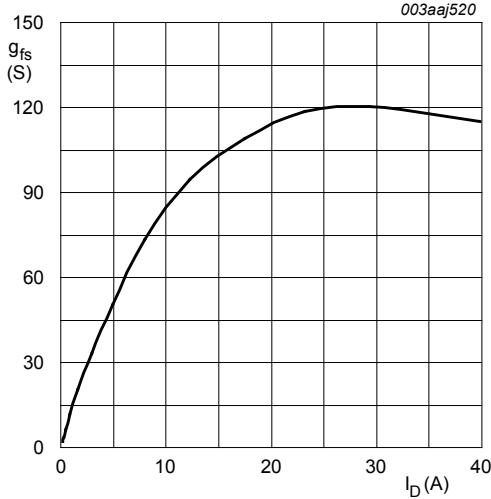


Fig. 6. Forward transconductance as a function of drain current; typical values

$T_j = 25 \text{ }^\circ\text{C}$ ;  $V_{DS} = 15 \text{ V}$

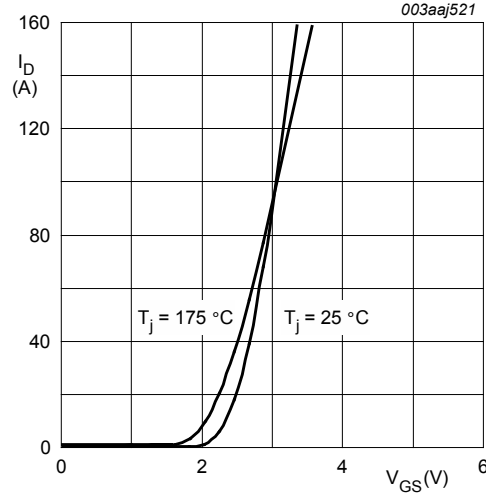


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 10 \text{ V}$

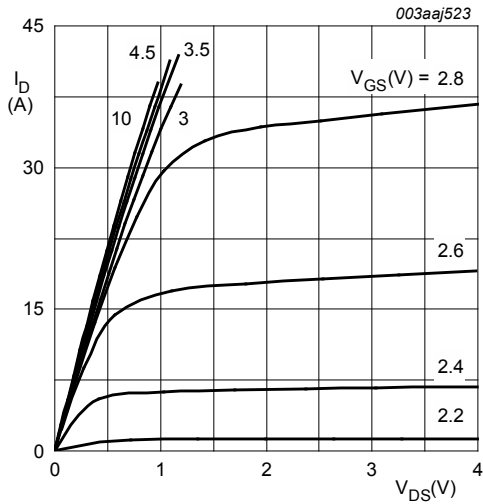


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25 \text{ }^\circ\text{C}$

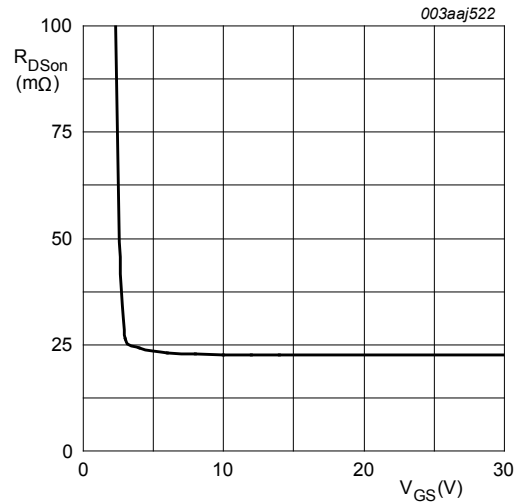
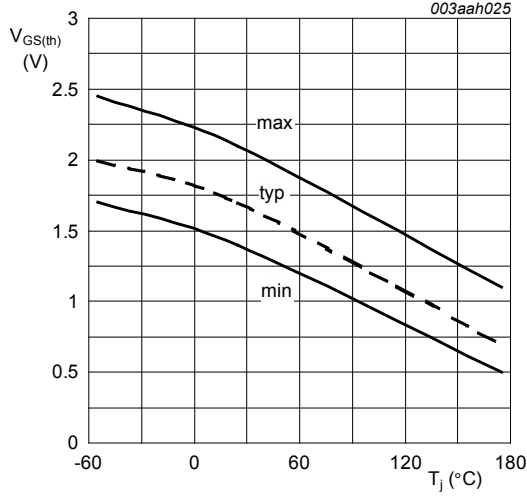


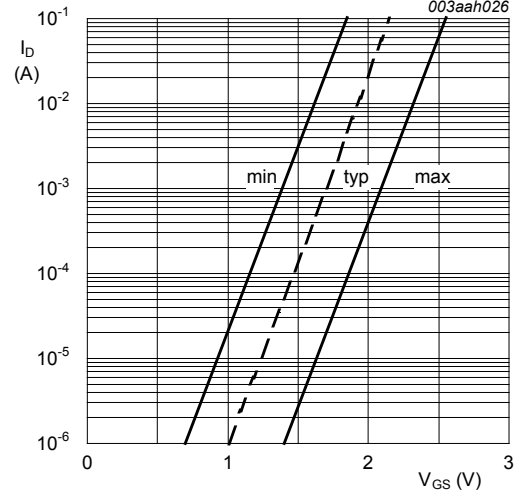
Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25 \text{ }^\circ\text{C}$ ;  $I_D = 5 \text{ A}$



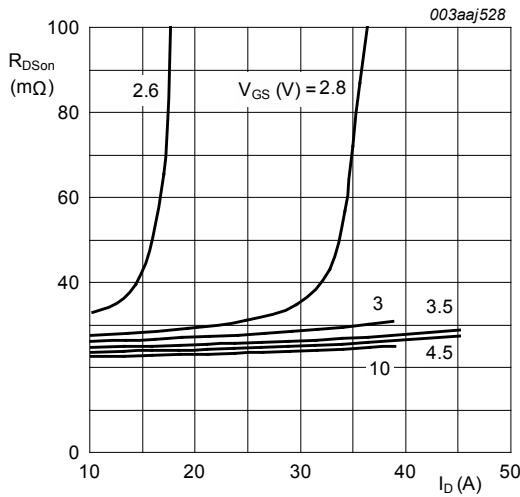
**Fig. 10. Gate-source threshold voltage as a function of junction temperature**

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$



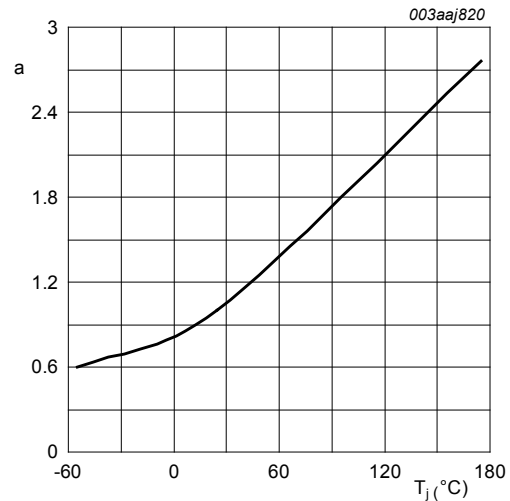
**Fig. 11. Sub-threshold drain current as a function of gate-source voltage**

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$



**Fig. 12. Drain-source on-state resistance as a function of drain current; typical values**

$$T_j = 25^\circ\text{C}$$



**Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$



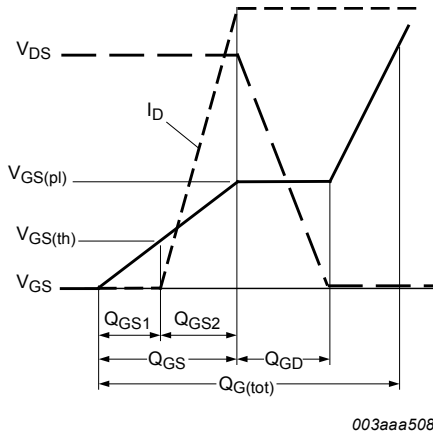


Fig. 14. Gate charge waveform definitions

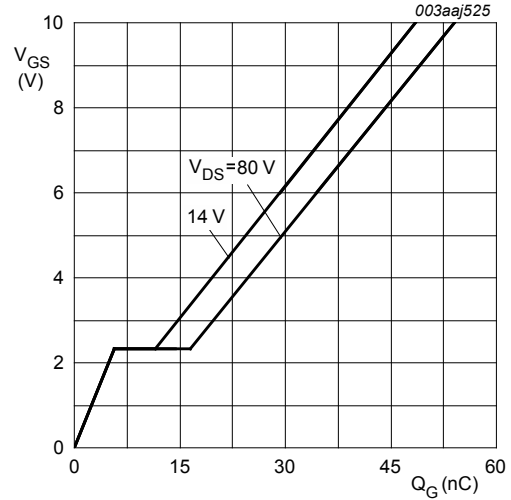


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 10\text{A}$

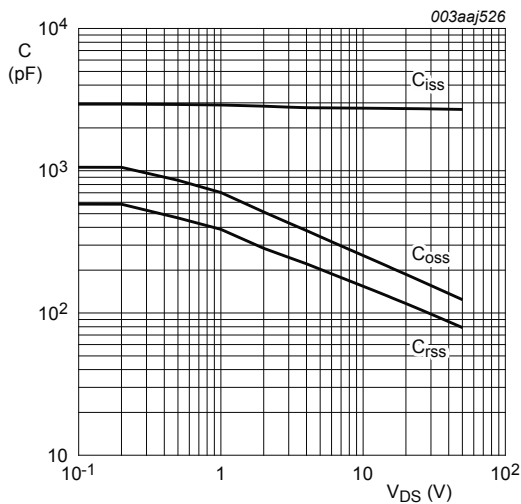


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{V}; f = 1\text{MHz}$

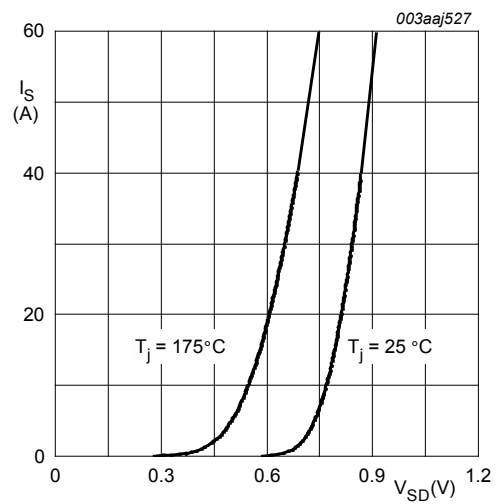


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{V}$

### 11. Package outline

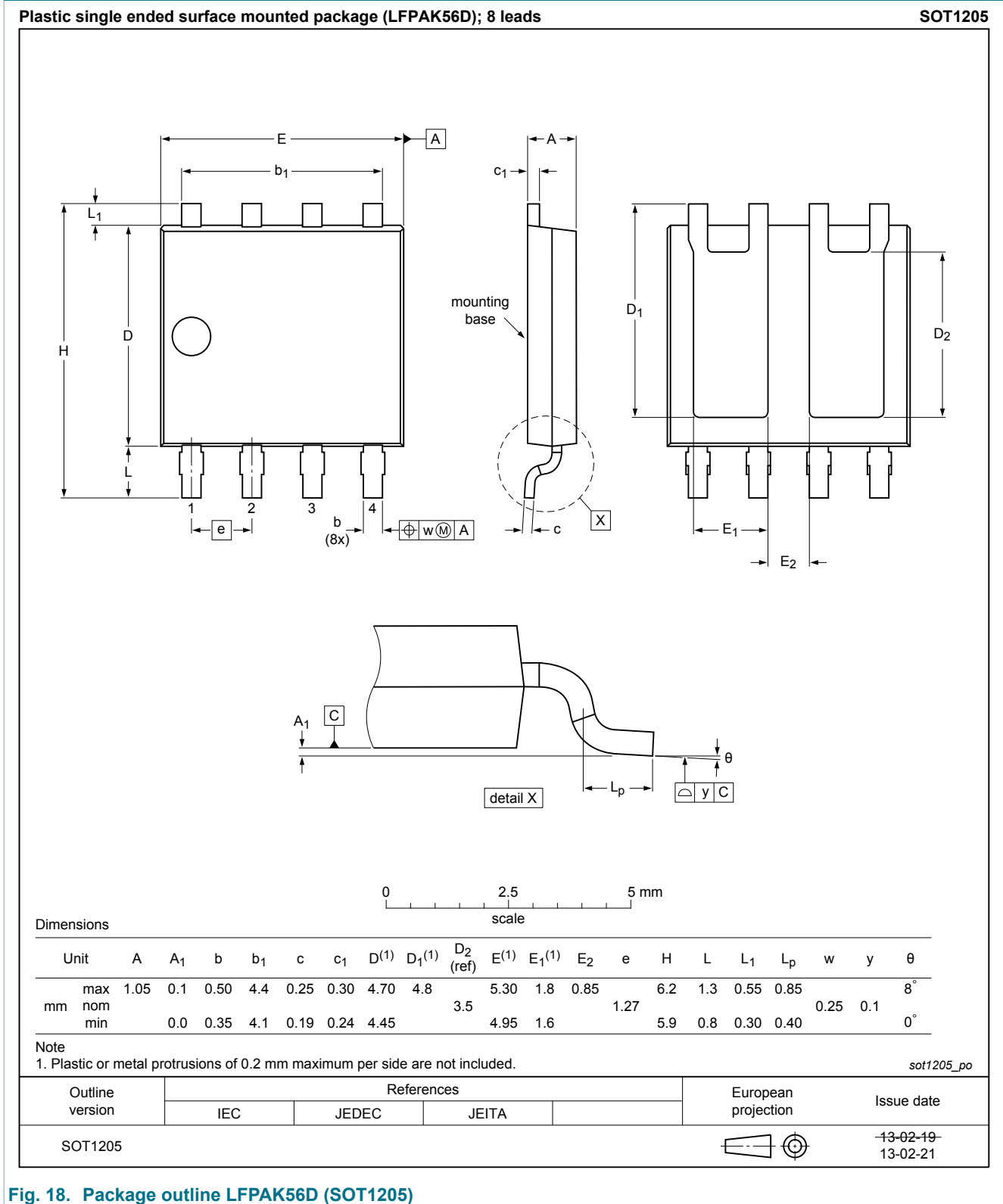


Fig. 18. Package outline LPAK56D (SOT1205)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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